

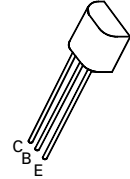
NPN SILICON PLANAR MEDIUM POWER HIGH CURRENT TRANSISTOR

ISSUE 1 – APRIL 94

FEATURES

- * 300 Volt V_{CEO}
- * 3 Amps continuous current
- * Up to 5 Amps peak current
- * Very low saturation voltage
- * $P_{tot} = 1.2$ Watt

ZTX857



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	330	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	6	V
Peak Pulse Current	I_{CM}	5	A
Continuous Collector Current	I_C	3	A
Practical Power Dissipation*	P_{totp}	1.58	W
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1.2	W
Operating and Storage Temperature Range	$T_j: T_{stg}$	-55 to +200	$^{\circ}C$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	330	475		V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	330	475		V	$I_C=1\mu A, R_B \leq 1K\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	300	350		V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	8		V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}			50 1	nA μA	$V_{CB}=300V$ $V_{CB}=300V, T_{amb}=100^{\circ}C$
Collector Cut-Off Current	I_{CER} $R \leq 1K\Omega$			50 1	nA μA	$V_{CB}=300V$ $V_{CB}=300V, T_{amb}=100^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			10	nA	$V_{EB}=6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		50 80 140 170	100 140 200 250	mV mV mV mV	$I_C=0.5A, I_B=50mA^*$ $I_C=1A, I_B=100mA^*$ $I_C=2A, I_B=200mA^*$ $I_C=3A, I_B=600mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		870	1000	mV	$I_C=2A, I_B=200mA^*$

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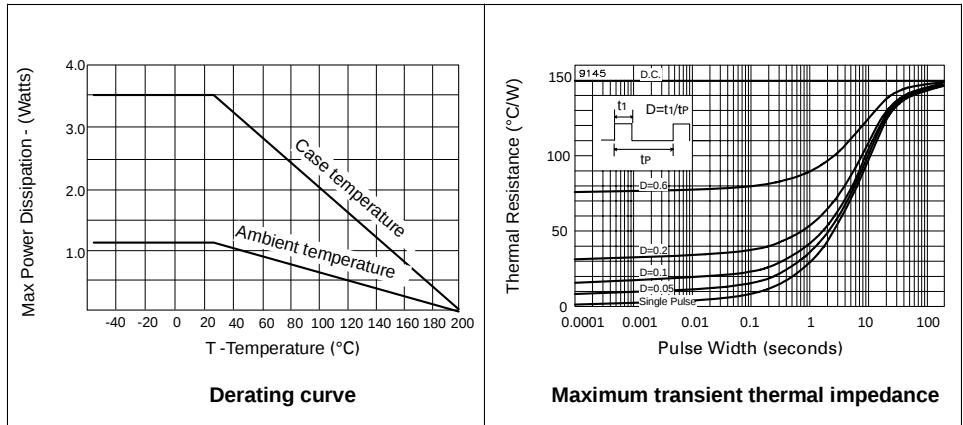
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		810	950	mV	$I_C=2A, V_{CE}=5V^*$
Static Forward Current Transfer Ratio	h_{FE}	100 100 15	200 200 25 15	300		$I_C=10mA, V_{CE}=5V$ $I_C=500mA, V_{CE}=10V^*$ $I_C=2A, V_{CE}=10V^*$ $I_C=3A, V_{CE}=10V^*$
Transition Frequency	f_T		80		MHz	$I_C=100mA, V_{CE}=10V$ $f=100MHz$
Output Capacitance	C_{obo}		11		pF	$V_{CB}=20V, f=1MHz$
Switching Times	t_{on} t_{off}		100 5300		ns ns	$I_C=250mA, I_{B1}=25mA$ $I_{B2}=25mA, V_{CC}=50V$

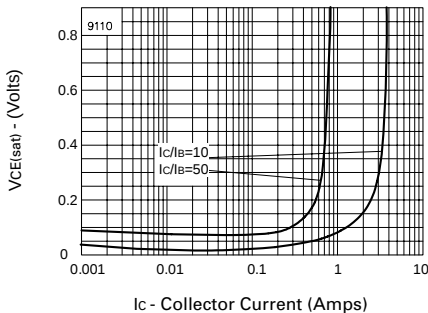
*Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle $\leq 2\%$

THERMAL CHARACTERISTICS

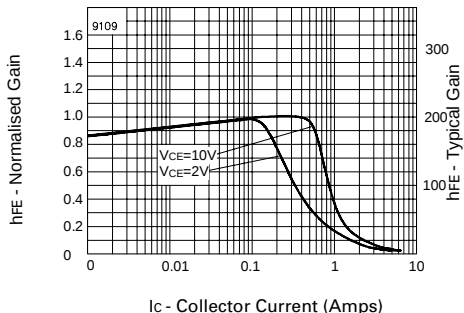
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient	$R_{th(j-amb)}$	150	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	50	$^{\circ}\text{C/W}$



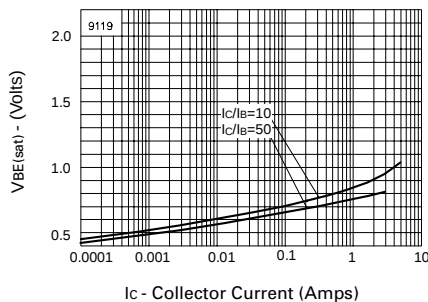
TYPICAL CHARACTERISTICS



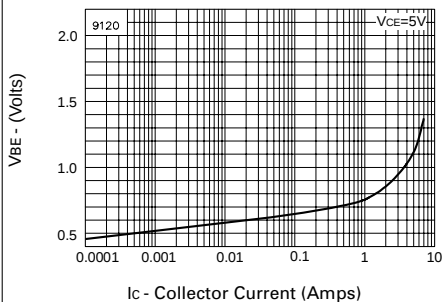
$V_{CE(sat)}$ v I_C



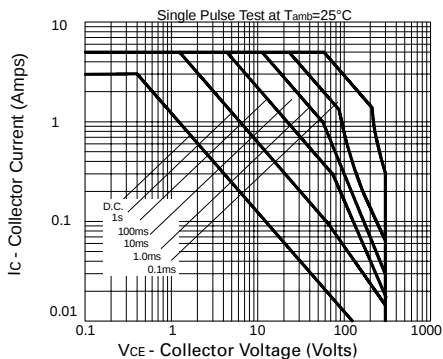
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area